ABSTRACT OF THE DISCLOSURE

A wafer for charge amount evaluation having a silicon substrate and p-type regions sandwiched between a first silicon oxide film and a SA-NSG film and surrounded by an undoped silicon film is prepared and subjected to a target process for which an amount of charge is to be evaluated. Then, etching is performed by using a BHF solution. By measuring an amount of etching in the p-type region, an amount of positive charge caused by the process in the wafer can be evaluated quantitatively in an easy and convenient manner.